

General Description

The WSF25N20 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the synchronous buck converter applications.

The WSF25N20 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Green Device Available

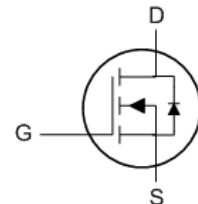
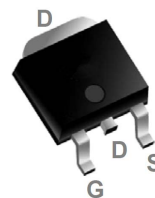
Product Summary

BV _{DSS}	R _{DS(on)}	I _D
200V	60mΩ	25A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

TO-252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	200	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	25	A
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	16	A
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.7	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	3.0	A
I _{DM}	Pulsed Drain Current ²	75	A
EAS	Single Pulse Avalanche Energy ³	35	mJ
I _{AS}	Avalanche Current	6.5	A
P _D @T _C =25°C	Total Power Dissipation ³	113	W
P _D @T _C =100°C	Total Power Dissipation ³	45	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	50	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	---	1.1	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	200	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.098	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =12A	---	60	75	mΩ
		V _{GS} =6.0V, I _D =10A	---	85	150	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =160V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =160V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±25V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =8A	---	20	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2	4	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =100V, V _{GS} =10V, I _D =12A	---	40	---	nC
Q _{gs}	Gate-Source Charge		---	14	---	
Q _{gd}	Gate-Drain Charge		---	10	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =6Ω, I _D =12A, R _L =30Ω	---	16	---	ns
T _r	Rise Time		---	7	---	
T _{d(off)}	Turn-Off Delay Time		---	37	---	
T _f	Fall Time		---	15	---	
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	---	2350	---	pF
C _{oss}	Output Capacitance		---	155	---	
C _{rss}	Reverse Transfer Capacitance		---	45	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.5mH, I _{AS} =6.5A	10	---	---	mJ

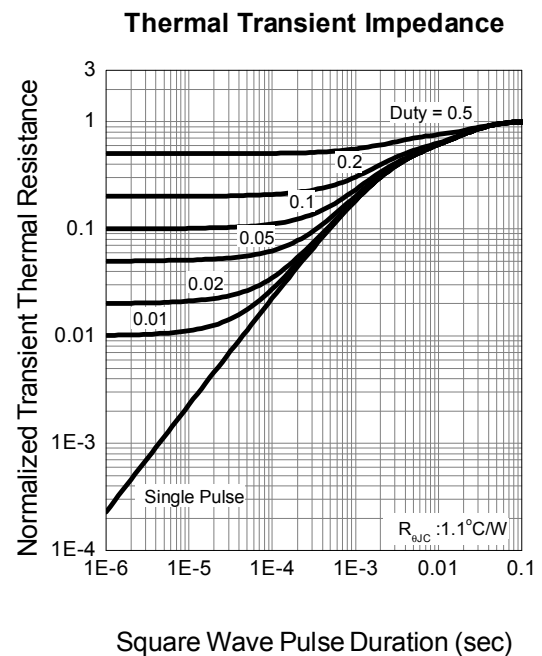
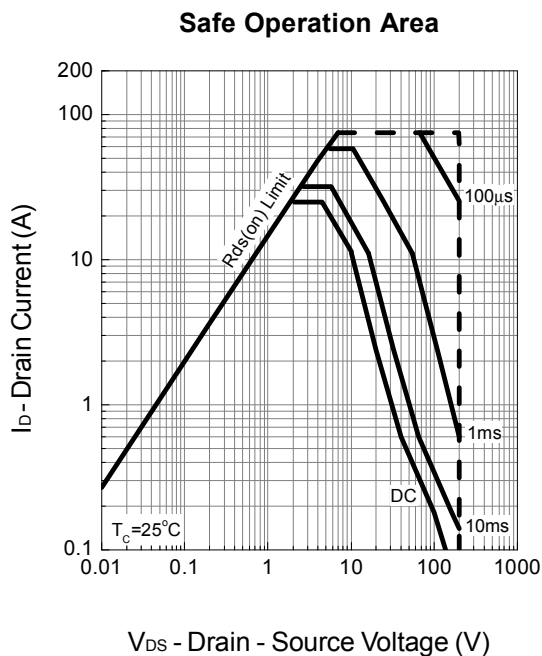
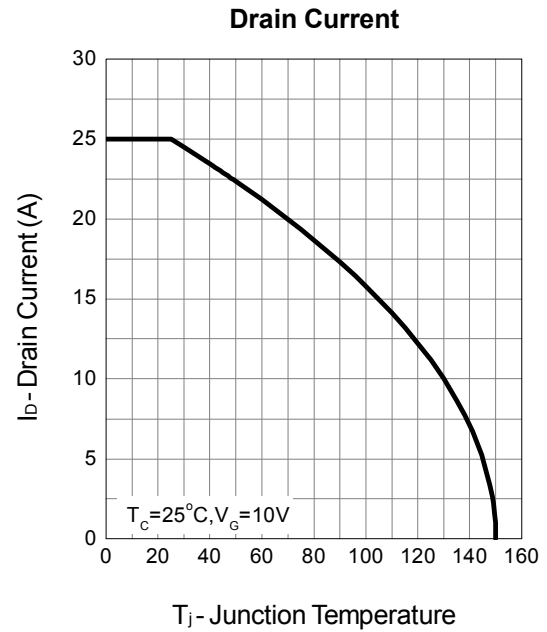
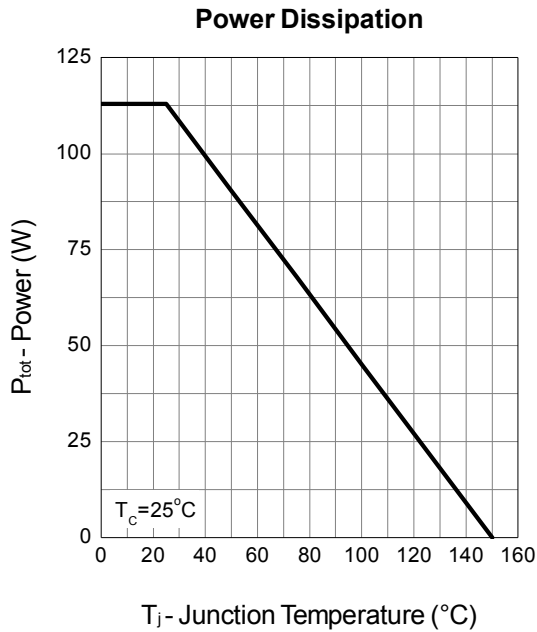
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	12	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	36	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =12A, T _J =25°C	---	---	1.3	V
t _{rr}	Reverse Recovery Time	I _F =12A, dI/dt=100A/μs, T _J =25°C	---	75	---	nS
Q _{rr}	Reverse Recovery Charge		---	250	---	nC

Note :

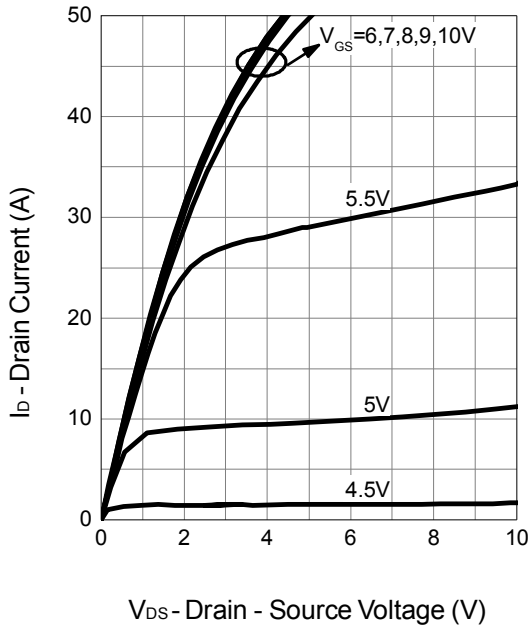
- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<=10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH, I_{AS}=6.5A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

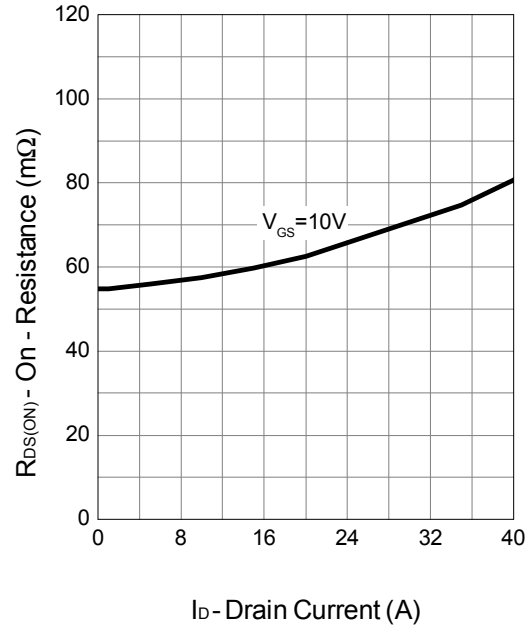


Typical Characteristics

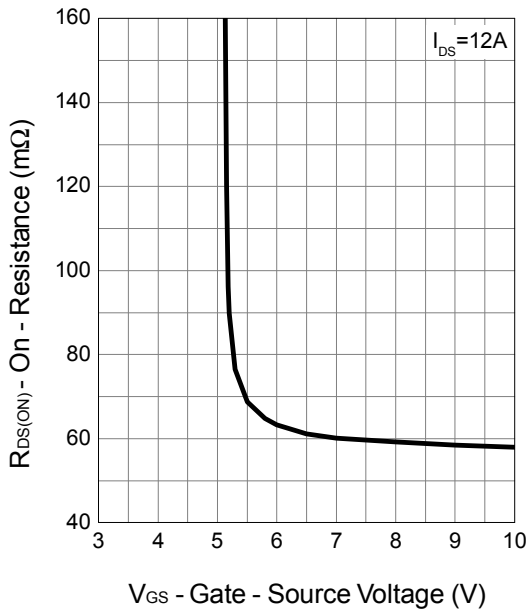
Output Characteristics



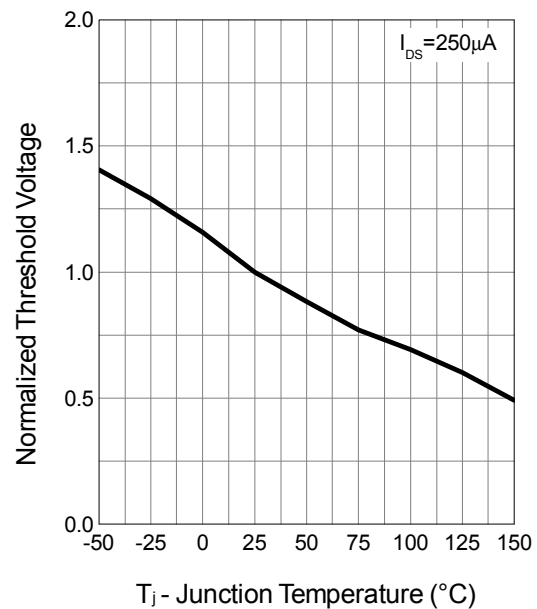
Drain-Source On Resistance



Gate-Source On Resistance

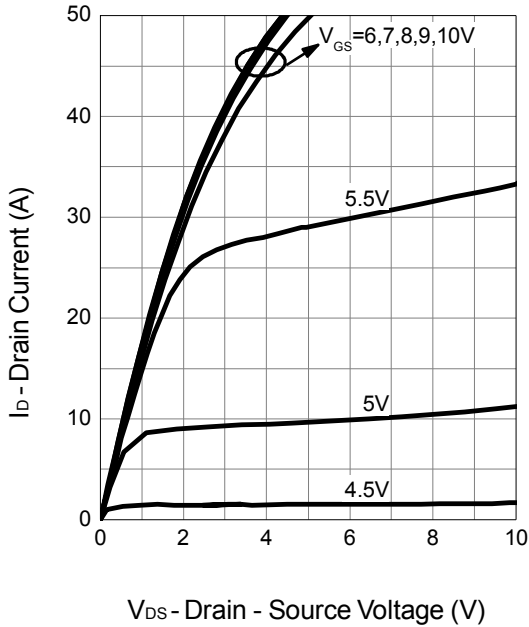


Gate Threshold Voltage

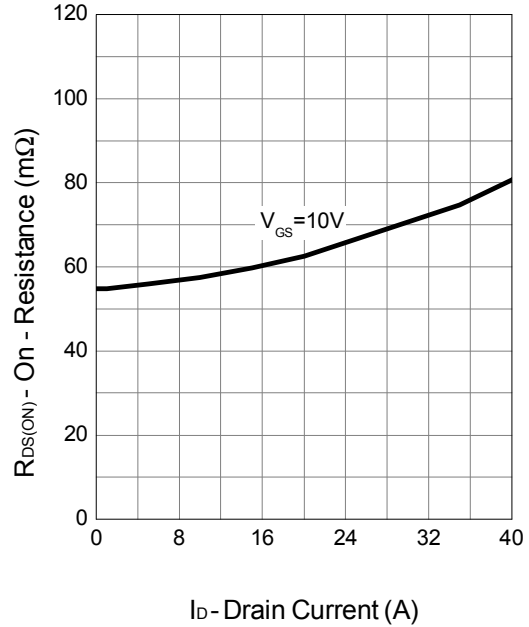


Typical Characteristics

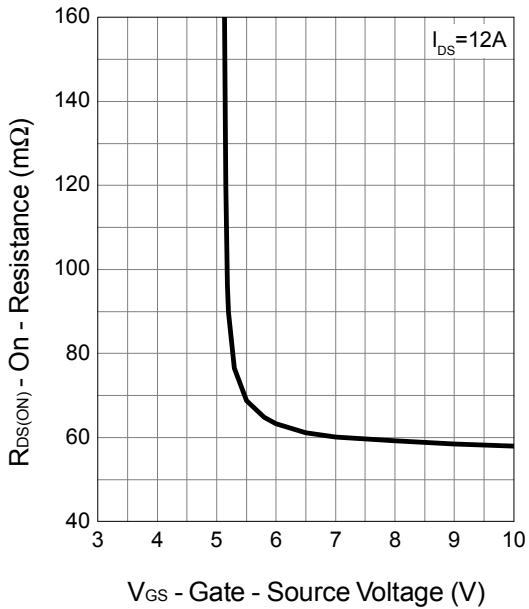
Output Characteristics



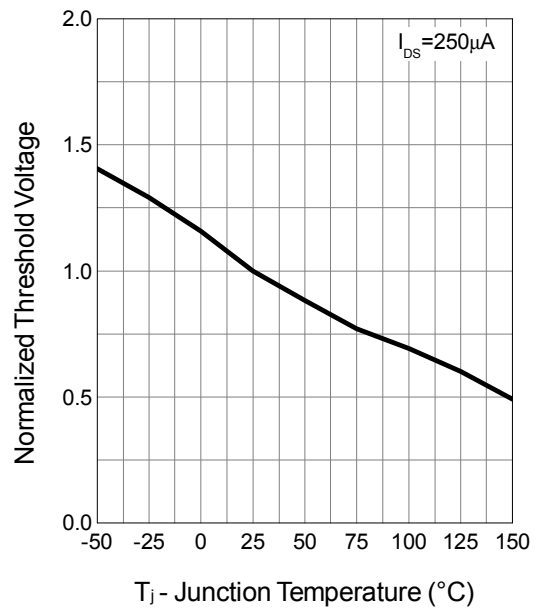
Drain-Source On Resistance



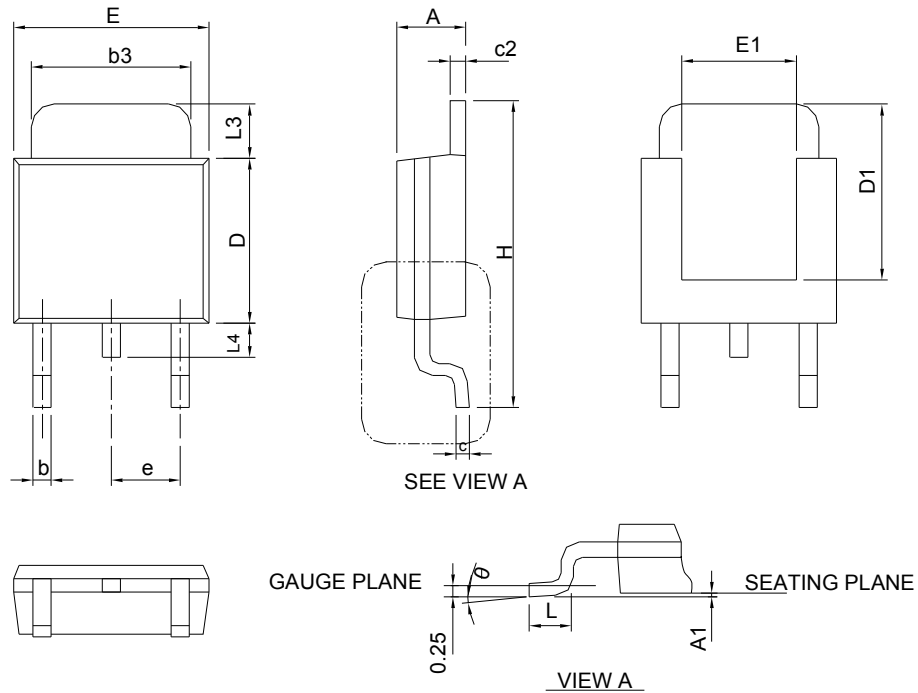
Gate-Source On Resistance



Gate Threshold Voltage

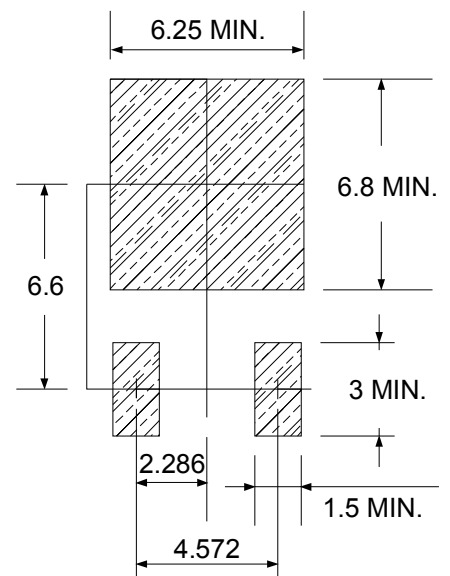


TO-252 Package Information



SYMBOL	TO-252			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	-	0.13	-	0.005
b	0.50	0.89	0.020	0.035
b3	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c2	0.46	0.89	0.018	0.035
D	5.33	6.22	0.210	0.245
D1	4.57	6.00	0.180	0.236
E	6.35	6.73	0.250	0.265
E1	3.81	6.00	0.150	0.236
e	2.29 BSC		0.090 BSC	
H	9.40	10.41	0.370	0.410
L	0.90	1.78	0.035	0.070
L3	0.89	2.03	0.035	0.080
L4	-	1.02	-	0.040
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm

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